

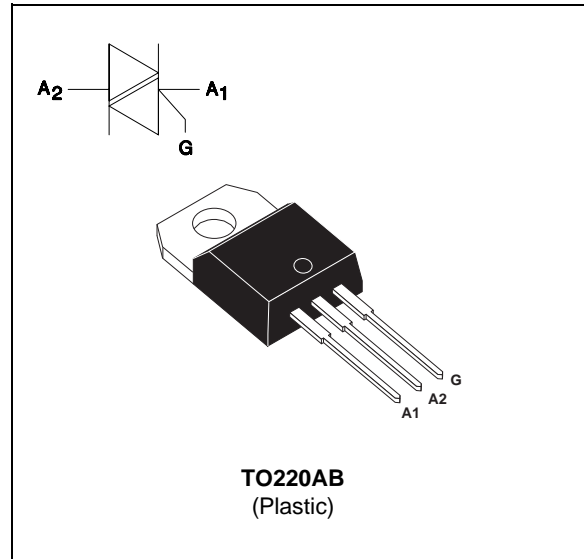
## SNUBBERLESS TRIACS

### FEATURES

- HIGH COMMUTATION :  $(di/dt)_c > 22A/ms$  without snubber
- HIGH SURGE CURRENT :  $I_{TSM} = 250A$
- $V_{DRM}$  UP TO 800V
- BTA family:  
Insulated voltage = 2500V<sub>(RMS)</sub>  
(UL RECOGNIZED : E81734)

### DESCRIPTION

The BTA/BTB24 BW/CW triac family are high performance glass passivated chips technology. The SNUBBERLESS™ concept offers suppression of RC network and it is suitable for application such as phase control and static switching on inductive or resistive load.



### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit	
$I_T(RMS)$	RMS on-state current (360° conduction angle)	BTA	$T_c = 75\text{ °C}$	25	A
		BTB	$T_c = 95\text{ °C}$	25	A
$I_{TSM}$	Non repetitive surge peak on-state current ( $T_j$ initial = 25°C )		$t_p = 8.3\text{ ms}$	260	A
			$t_p = 10\text{ ms}$	250	
$I_2t$	$I_2t$ value		$t_p = 10\text{ ms}$	312	A <sup>2</sup> s
$di/dt$	Critical rate of rise of on-state current Gate supply : $I_G = 500mA$ $di_G/dt = 1A/\mu s$		Repetitive $F = 50\text{ Hz}$	20	A/ $\mu s$
			Non Repetitive	100	
$T_{stg}$ $T_j$	Storage and operating junction temperature range			- 40 to + 150 - 40 to + 125	°C °C
$T_I$	Maximum lead temperature for soldering during 10 s at 4.5 mm from case			260	°C

Symbol	Parameter	BTA/BTB24-... BW/CW			Unit
		600	700	800	
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltage $T_j = 125\text{ °C}$	600	700	800	V

## BTA/BTB24 BW/CW

### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient		60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	2.3	°C/W
		BTB	1.3	°C/W
Rth (j-c) AC	Junction to case for 360° conduction angle (F= 50 Hz)	BTA	1.7	°C/W
		BTB	1.0	°C/W

### GATE CHARACTERISTICS (maximum values)

$P_G (AV) = 1W$     $P_{GM} = 10W$  ( $t_p = 20 \mu s$ )    $I_{GM} = 4A$  ( $t_p = 20 \mu s$ ).

### ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Suffix		Unit
					BW	CW	
I <sub>GT</sub>	V <sub>D</sub> =12V (DC) R <sub>L</sub> =33Ω	T <sub>j</sub> =25°C	I-II-III	MIN	4	2	mA
				MAX	50	35	
V <sub>GT</sub>	V <sub>D</sub> =12V (DC) R <sub>L</sub> =33Ω	T <sub>j</sub> =25°C	I-II-III	MAX	1.3		V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> R <sub>L</sub> =3.3kΩ	T <sub>j</sub> =125°C	I-II-III	MIN	0.2		V
I <sub>L</sub>	I <sub>G</sub> =1.2 I <sub>GT</sub>	T <sub>j</sub> =25°C	I-III	MAX	60	50	mA
			II	MAX	120	80	
I <sub>H</sub> *	I <sub>T</sub> = 250mA gate open	T <sub>j</sub> =25°C		MAX	75	50	mA
V <sub>TM</sub> *	I <sub>TM</sub> = 35A t <sub>p</sub> = 380μs	T <sub>j</sub> =25°C		MAX	1.5		V
I <sub>DRM</sub> I <sub>RRM</sub>	V <sub>DRM</sub> Rated V <sub>RRM</sub> Rated	T <sub>j</sub> =25°C		MAX	5		μA
		T <sub>j</sub> =125°C		MAX	3		mA
dV/dt *	Linear slope up to V <sub>D</sub> =67%V <sub>DRM</sub> gate open	T <sub>j</sub> =125°C		MIN	1000	500	V/μs
(dI/dt) <sub>c</sub> *	Without snubber	T <sub>j</sub> =125°C		MIN	22	13	A/ms

\* For either polarity of electrode A2 voltage with reference to electrode A1.

ORDERING INFORMATION

Package	IT(RMS)	VDRM / VRRM	Sensitivity Specification		
	A		V	BW	CW
BTA (Insulated)	25	600	X	X	
			700	X	X
			800	X	X
BTB (Uninsulated)	25	600	X	X	
			700	X	X
			800	X	X

Fig.1 : Maximum RMS power dissipation versus RMS on-state current.

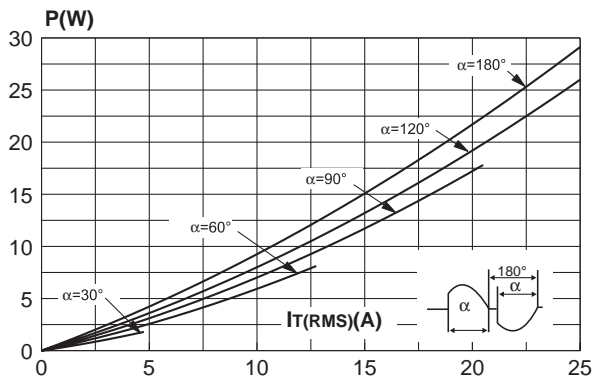


Fig.2 : Correlation between maximum power dissipation and maximum allowable temperatures (Tamb and Tcase) for different thermal resistances heatsink + contact. (BTA)

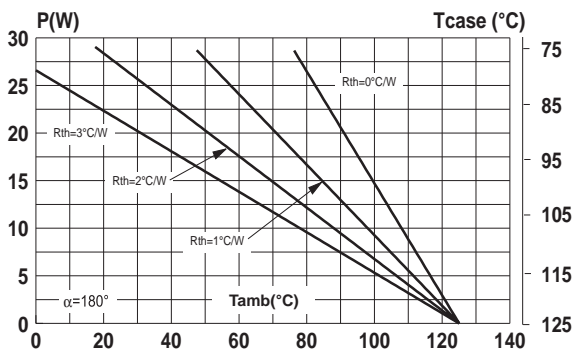


Fig.3 : Correlation between maximum power dissipation and maximum allowable temperatures (Tamb and Tcase) for different thermal resistances heatsink + contact.(BTB)

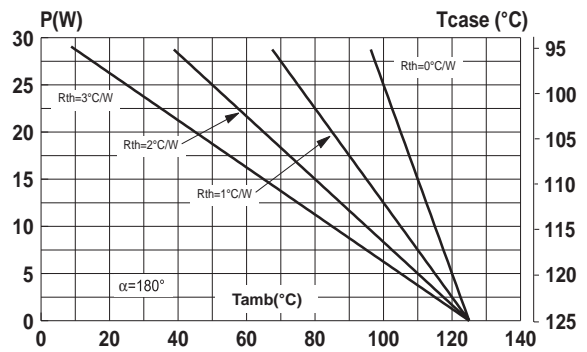


Fig.4 : RMS on-state current versus case temperature.

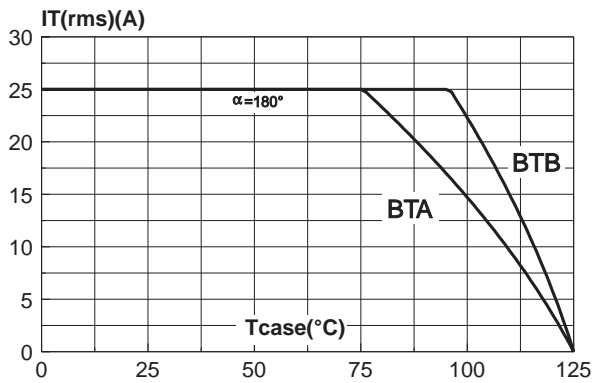


Fig.5 : Relative variation of thermal impedance versus pulse duration.

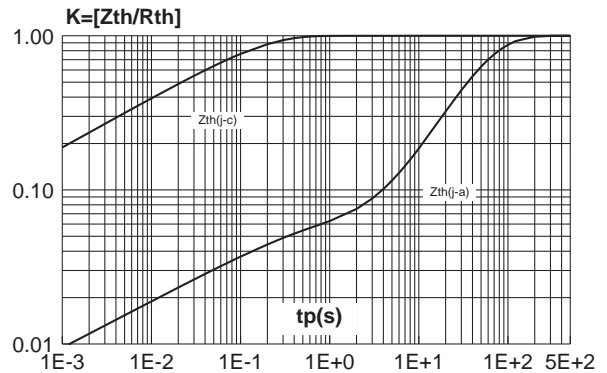


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature (typical values).

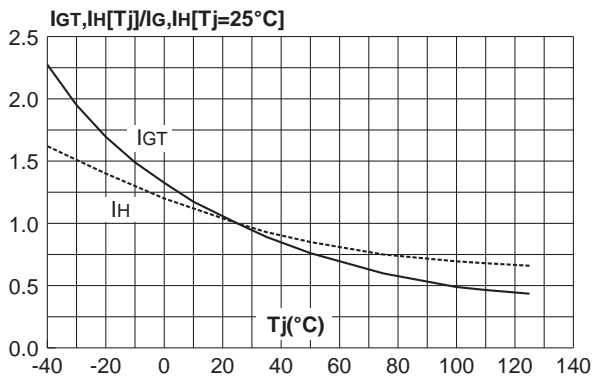


Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

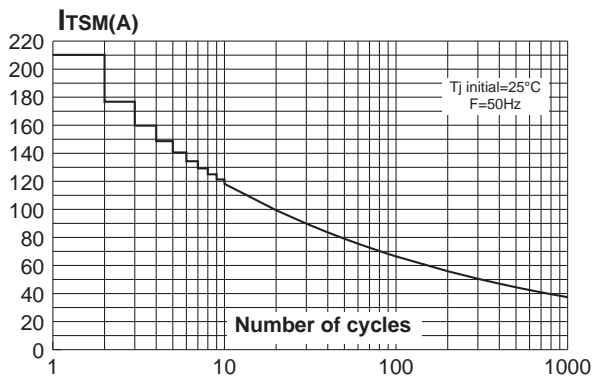


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width :  $tp \leq 10ms$ , and corresponding value of  $I^2t$ .

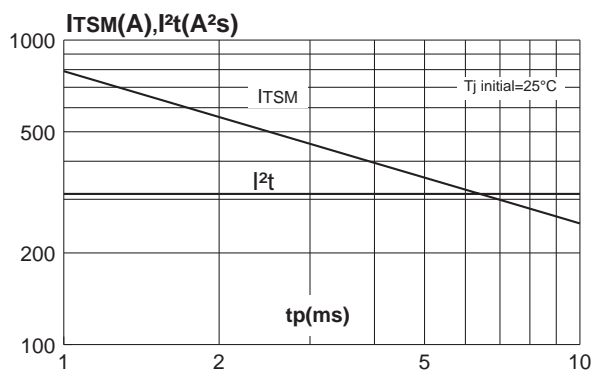
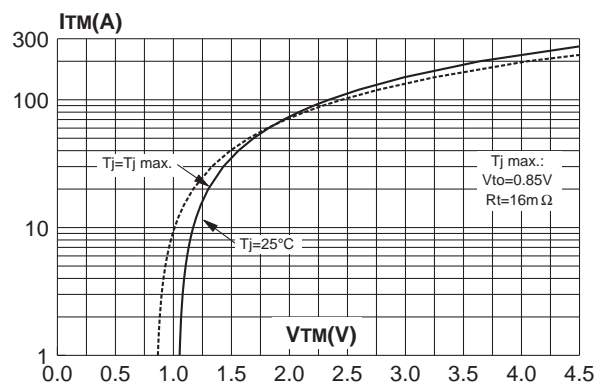
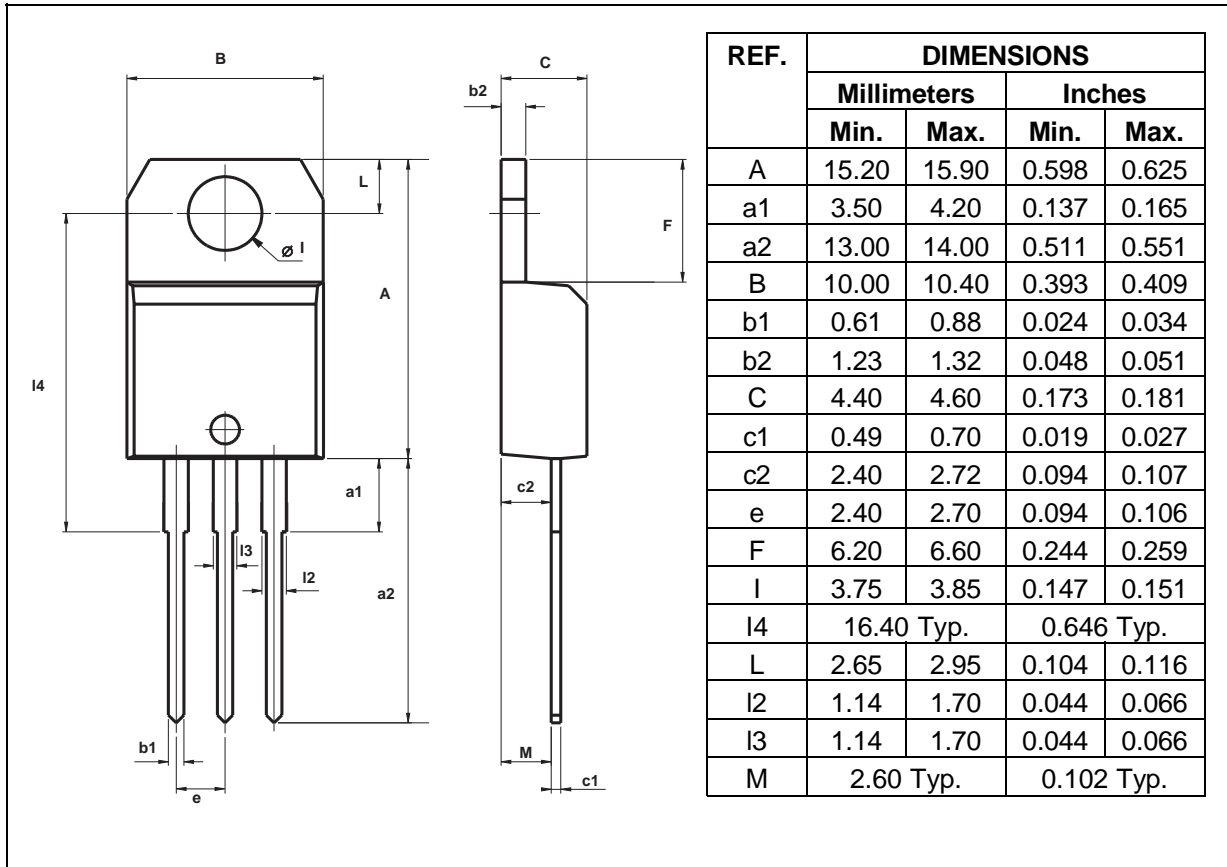


Fig.9 : On-state characteristics (maximum values).



**PACKAGE MECHANICAL DATA**

TO220AB Plastic



Cooling method : C  
 Marking : type number  
 Weight : 2.1 g  
 Recommended torque value : 0.8 m.N.  
 Maximum torque value : 1 m.N.

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